



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	0.85Ω@10V	0.34A
	0.95Ω@4.5V	

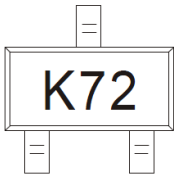
#### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge

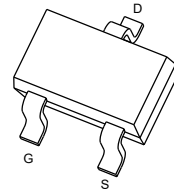
#### Application

- Load Switch
- DC/DC Converter

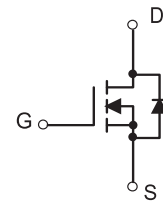
#### MARKING:



#### SOT-523



#### Schematic diagram



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	60	V
Gate - Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>1,5</sup>	$I_D$	0.34	A
	$T_A = 25^\circ\text{C}$		
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	1.0	A
Power Dissipation <sup>4,5</sup>	$P_D$	0.25	W
	$T_A = 25^\circ\text{C}$		
Thermal Resistance from Junction to Ambient <sup>5</sup>	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

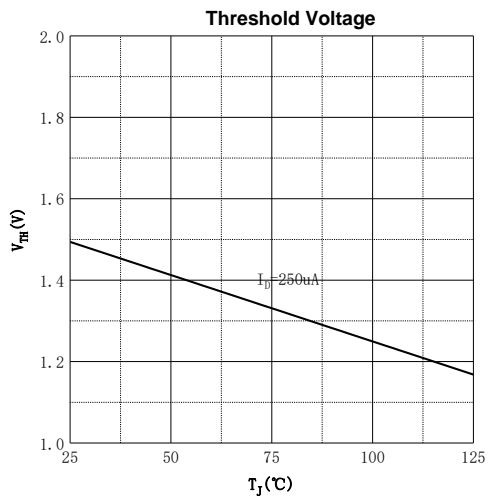
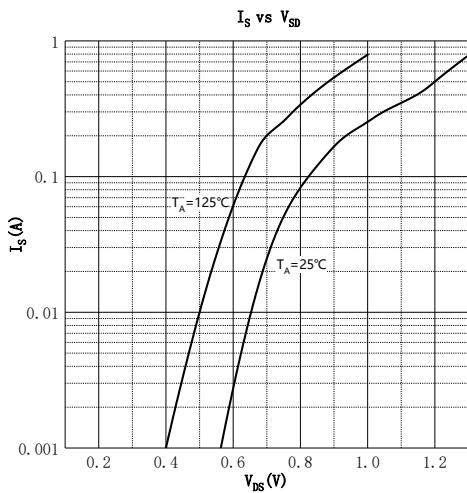
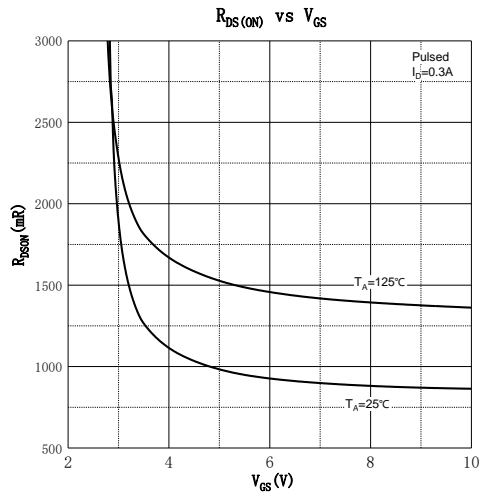
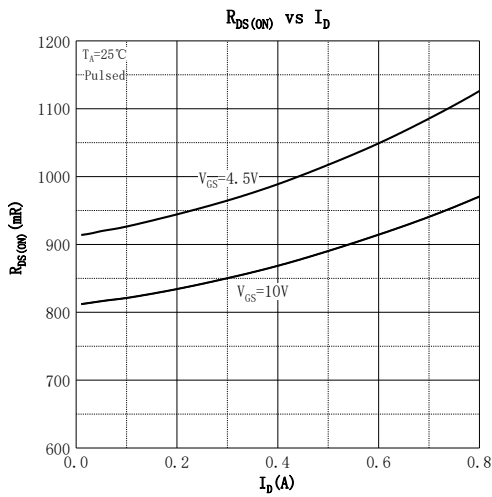
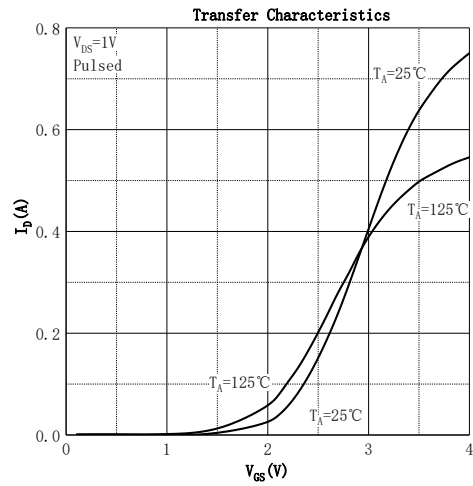
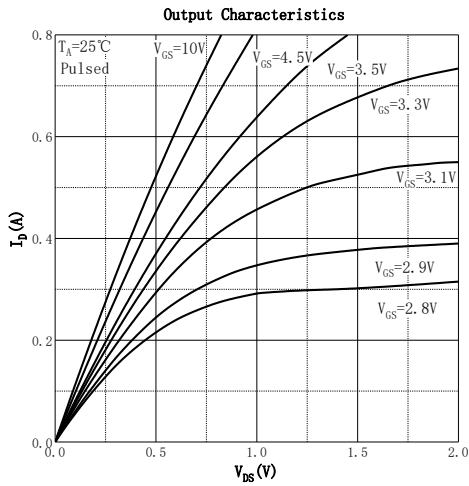
**MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 95$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.3A$		0.85	2.5	$\Omega$
		$V_{GS} = 4.5V, I_D = 0.2A$		0.95	3	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		34.8		pF
Output Capacitance	$C_{oss}$			6.4		
Reverse Transfer Capacitance	$C_{rss}$			3.5		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		40		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 30V, V_{GS} = 10V, I_D = 0.3A$		0.32		nC
Gate-source Charge	$Q_{gs}$			0.25		
Gate-drain Charge	$Q_{gd}$			0.17		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V,$ $R_L = 100\Omega, R_G = 3\Omega$		3.8		ns
Turn-on Rise Time	$t_r$			2.9		
Turn-off Delay Time	$t_{d(off)}$			14		
Turn-off Fall Time	$t_f$			8		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 0.3A$			1.2	V

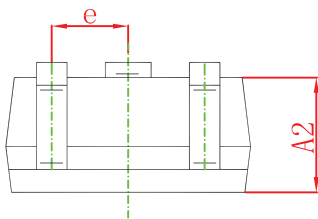
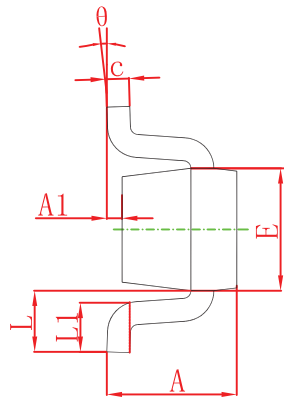
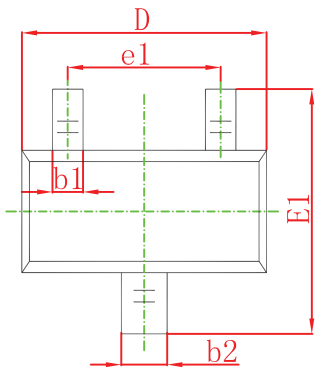
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .
- 5.Device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## Typical Characteristics



## SOT-523 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°